N-Channel Silicon MOSFET



2SK1898

Ultrahigh-Speed Switching Applications

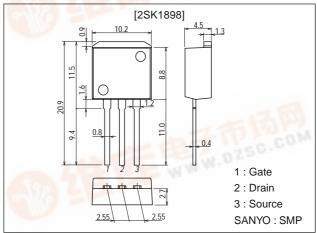
Features

- · Low ON resistance.
- · Ultrahigh-speed switching.
- · Low-voltage drive.
- · Surface mount type device making the following possible.
 - · Reduction in the number of manufacturing processes for 2SK1898-applied equipment.
- · High density surface mount applications.
- · Small size of 2SK1898-applied equipment.

Package Dimensions

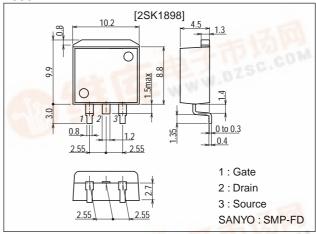
unit:mm

2093A



unit:mm

2090A



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Specifications

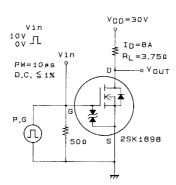
Absolute Maximum Ratings at Ta = 25°C

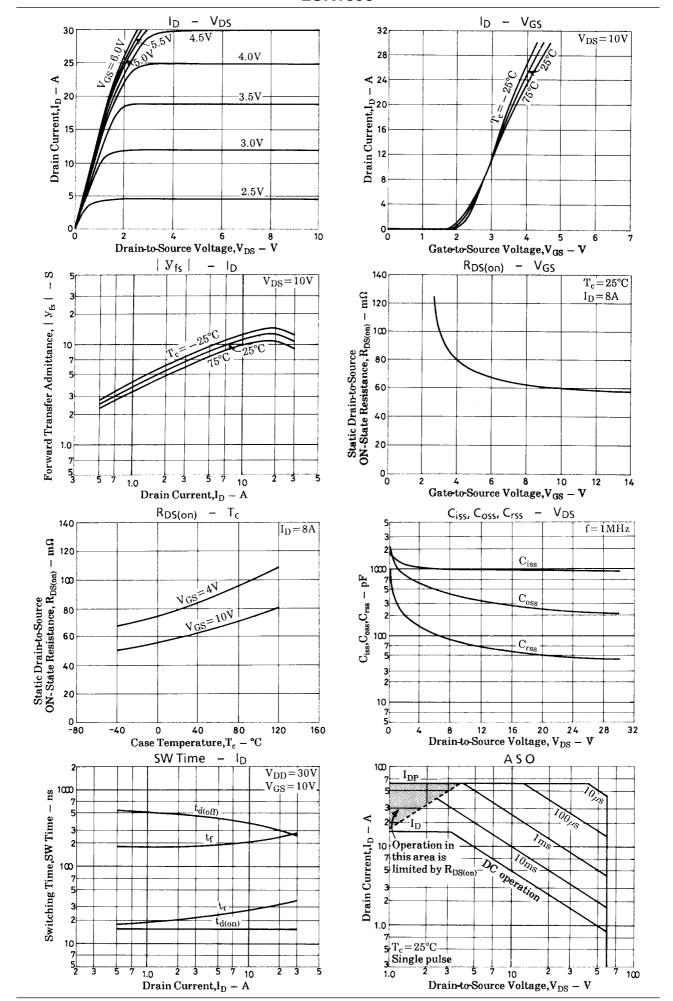
Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	VDSS		60	V
Gate-to-Source Voltage	VGSS		±15	V
Drain Current (DC)	I _D		15	Α
Drain Current (Pulse)	I _{DP}	PW≤10μs, duty cycle≤1%	60	Α
Allowable Power Dissipation	Po		1.65	W
	PD	Tc=25°C	50	W
Channel Temperature	Tch		150	°C
Storage Temperature	Tstg		-55 to +150	°C

Electrical Characteristics at Ta = 25°C

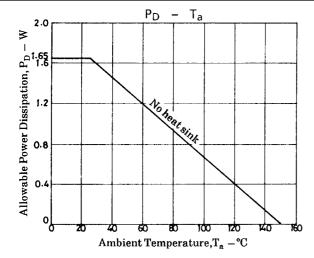
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	Offic
Drain-to-Source Breakdown Voltage	V(BR)DSS	I _D =1mA, V _{GS} =0	60			V
Gate-to-Source Breakdown Voltage	V(BR)GSS	I _G =±100μA, V _{DS} =0	±15			V
Zero-Gate Voltage Drain Current	IDSS	V _{DS} =60V, V _{GS} =0			100	μΑ
Gate-to-Source Leakage Current	IGSS	V _{GS} =±12V, V _{DS} =0			±10	μΑ
Cutoff Voltage	VGS(off)	V _{DS} =10V, I _D =1mA	1.0		2.0	V
Forward Transfer Admittance	yfs	V _{DS} =10V, I _D =8A	6.5	10.5		S
Static Drain-to-Source ON-State Resistance	R _{DS(on)}	I _D =8A, V _{GS} =10V		60	80	mΩ
	R _{DS(on)}	I _D =8A, V _{GS} =4V		80	110	mΩ
Input Capacitance	Ciss	V _{DS} =20V, f=1MHz		950		pF
Output Capacitance	Coss	V _{DS} =20V, f=1MHz		250		pF
Reverse Transfer Capacitance	Crss	V _{DS} =20V, f=1MHz		50		pF
Turn-ON Delay Time	t _d (on)	See specified Test Circuit		13		ns
Rise Time	t _r	See specified Test Circuit		40		ns
Turn-OFF Delay Time	t _d (off)	See specified Test Circuit		95		ns
Fall Time	t _f	See specified Test Circuit		80		ns
Diode Forward Voltage	V _{SD}	I _S =15A, V _{GS} =0		1.0	1.5	V

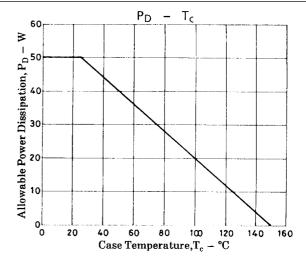
Switching Time Test Circuit





2SK1898





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